

Epi - Wafer

p-Type GaN

Feature	p-Type GaN Epi. Wafer Single side polished (Growth surface)
Diameter	2" (50.8mm)
Thickness (Included substrate)	~ 0.8 μm (+/-10% std)
Structure	p-GaN / u-GaN / Sapphire substrate



GaN on Sapphire Wafer

Characteristics (at 25°C)

Parameter		Typ.	Test Conditions
PL measurement	Peak wavelength	362nm \pm 2nm	Etamax PLATO Laser : 266nm
	Uniformity STD	<3%	
	FWHM	<10nm	
	FWHM STD	<3%	
Thickness	Thickness	~ 0.8 μm (+/-10% std)	Panalytical HRXRD
	Thickness STD	<10%	
XRD	(002)	N/A	Accent HL5500
	(102)	N/A	
Hall	Carrier Concentration	N/A	-
	Mobility	N/A	
Doping material	Si	N/A	-
	Mg	used	

Normalized Single Spectrum(300 ~ 700nm)

